

# NTSV2080CT

## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.50\text{ V}$  at  $I_F = 5\text{ A}$

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

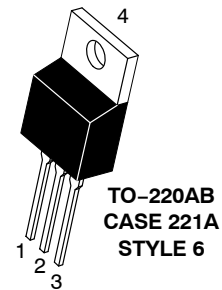
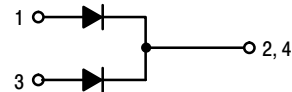
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



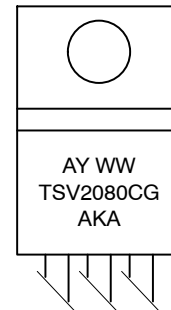
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### PIN CONNECTIONS



### MARKING DIAGRAMS



A	= Assembly Location
Y	= Year
WW	= Work Week
AKA	= Polarity Designator
G	= Pb-Free Package/Halide Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NTSV2080CT

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	80	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 130^\circ\text{C}$ )	$I_{F(AV)}$	20 10	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 125^\circ\text{C}$ )	$I_{FRM}$	40 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	100	A
Operating Junction Temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 70	$^\circ\text{C/W}$ $^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.55 0.65	- 0.98	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	20 10	600 20	$\mu\text{A}$ mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## ORDERING INFORMATION

Device	Package	Shipping
NTSV2080CTG	TO-220AB (Pb-Free/Halide Free)	50 Units / Rail

# NTSV2080CT

## TYPICAL CHARACTERISTICS

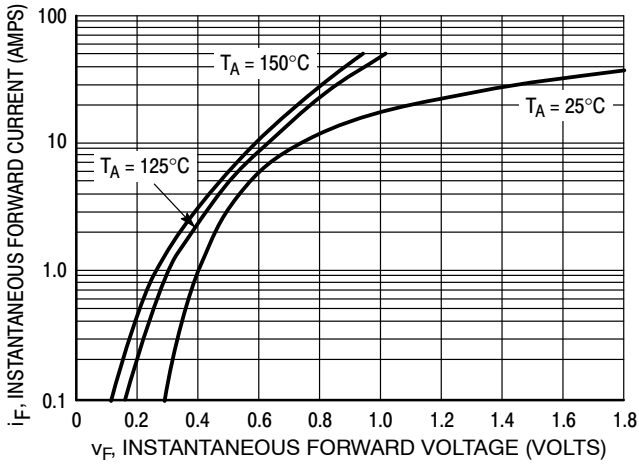


Figure 1. Typical Forward Voltage

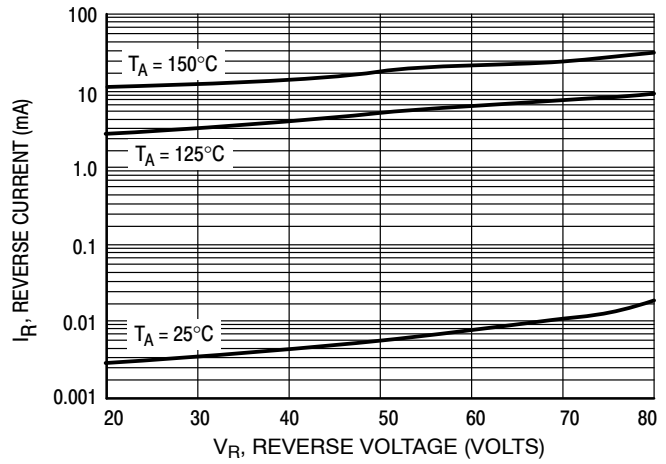


Figure 2. Typical Reverse Current

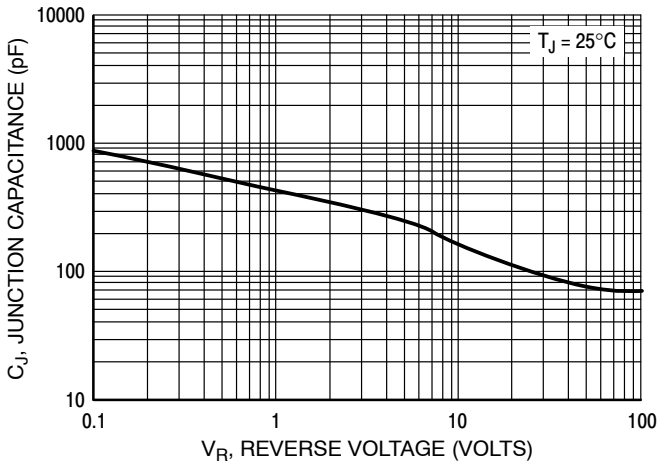


Figure 3. Typical Junction Capacitance

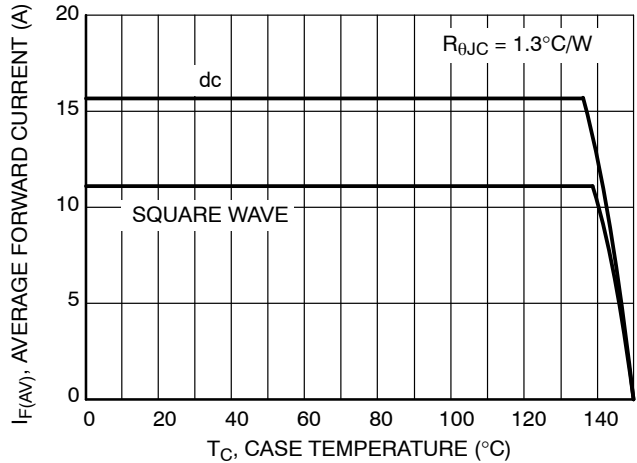


Figure 4. Current Derating per Leg

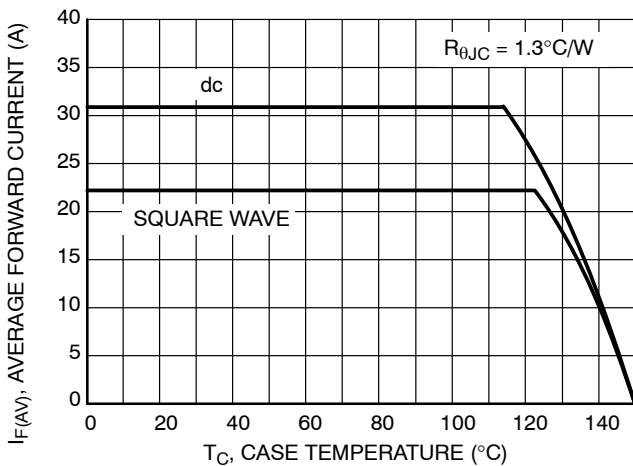


Figure 5. Current Derating

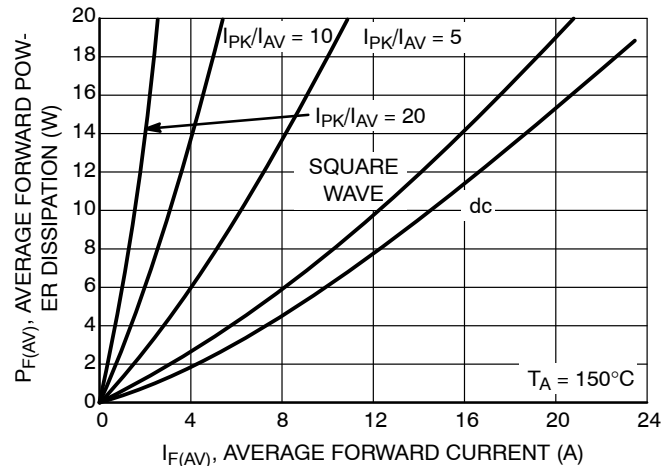


Figure 6. Forward Power Dissipation

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## TYPICAL CHARACTERISTICS

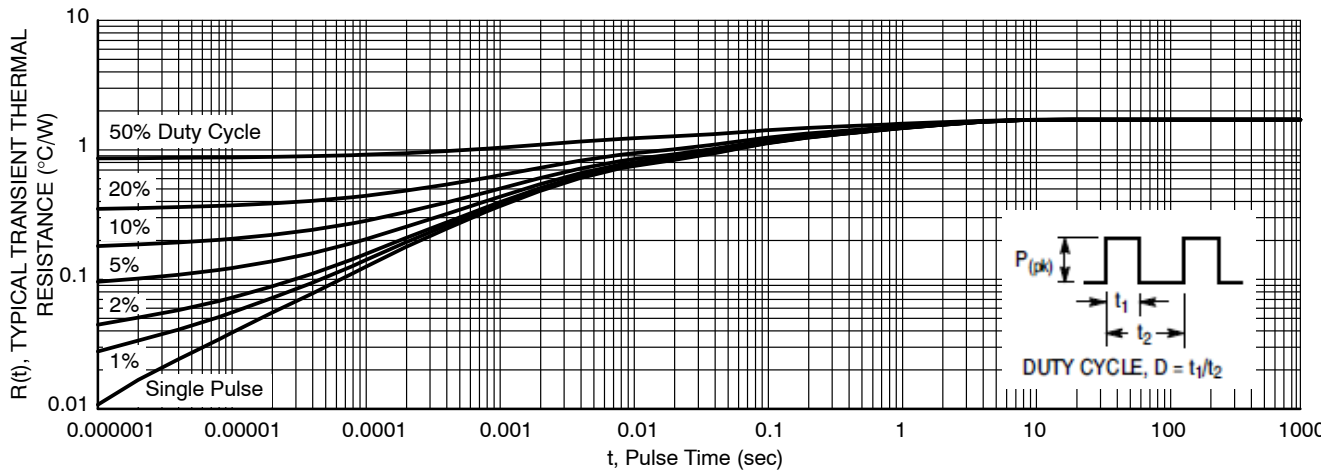
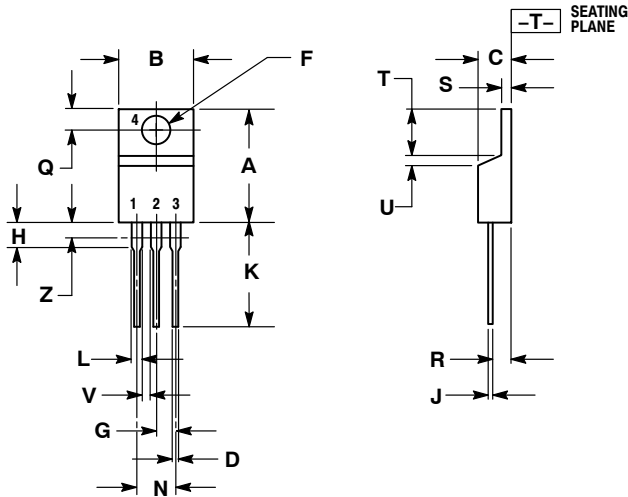


Figure 7. Typical Transient Thermal Response, Junction-to-Case

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## PACKAGE DIMENSIONS

### TO-220 CASE 221A-09 ISSUE AH




#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

#### STYLE 6:

1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

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